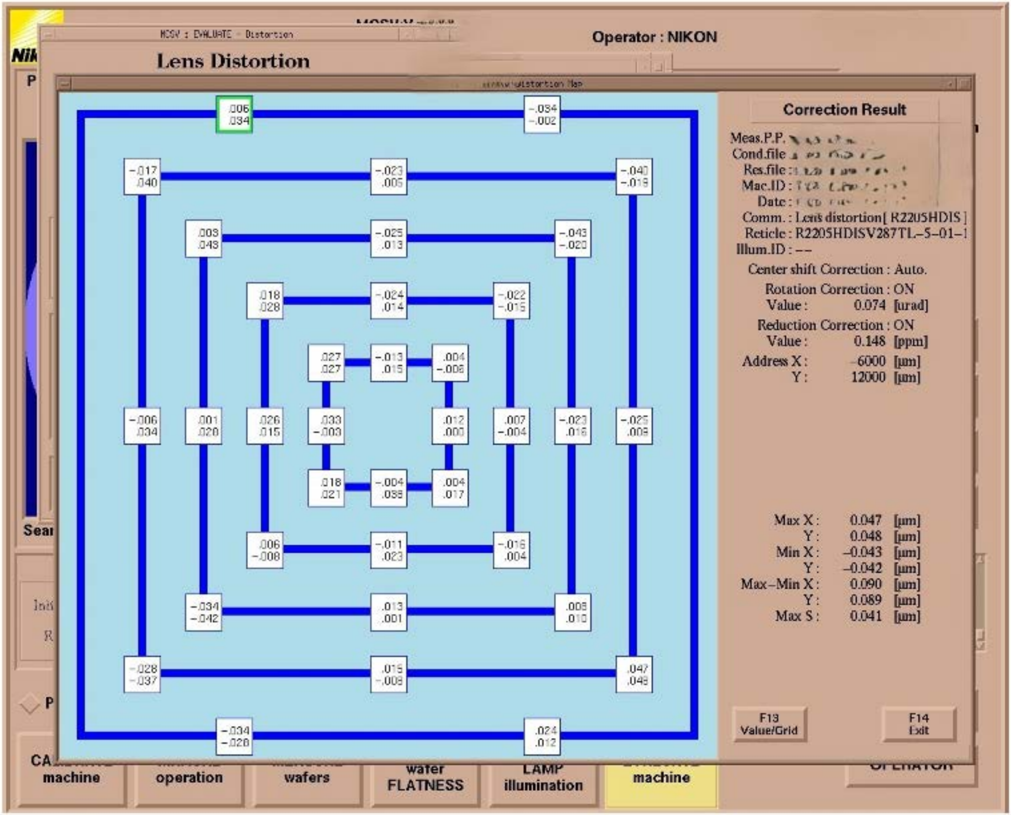
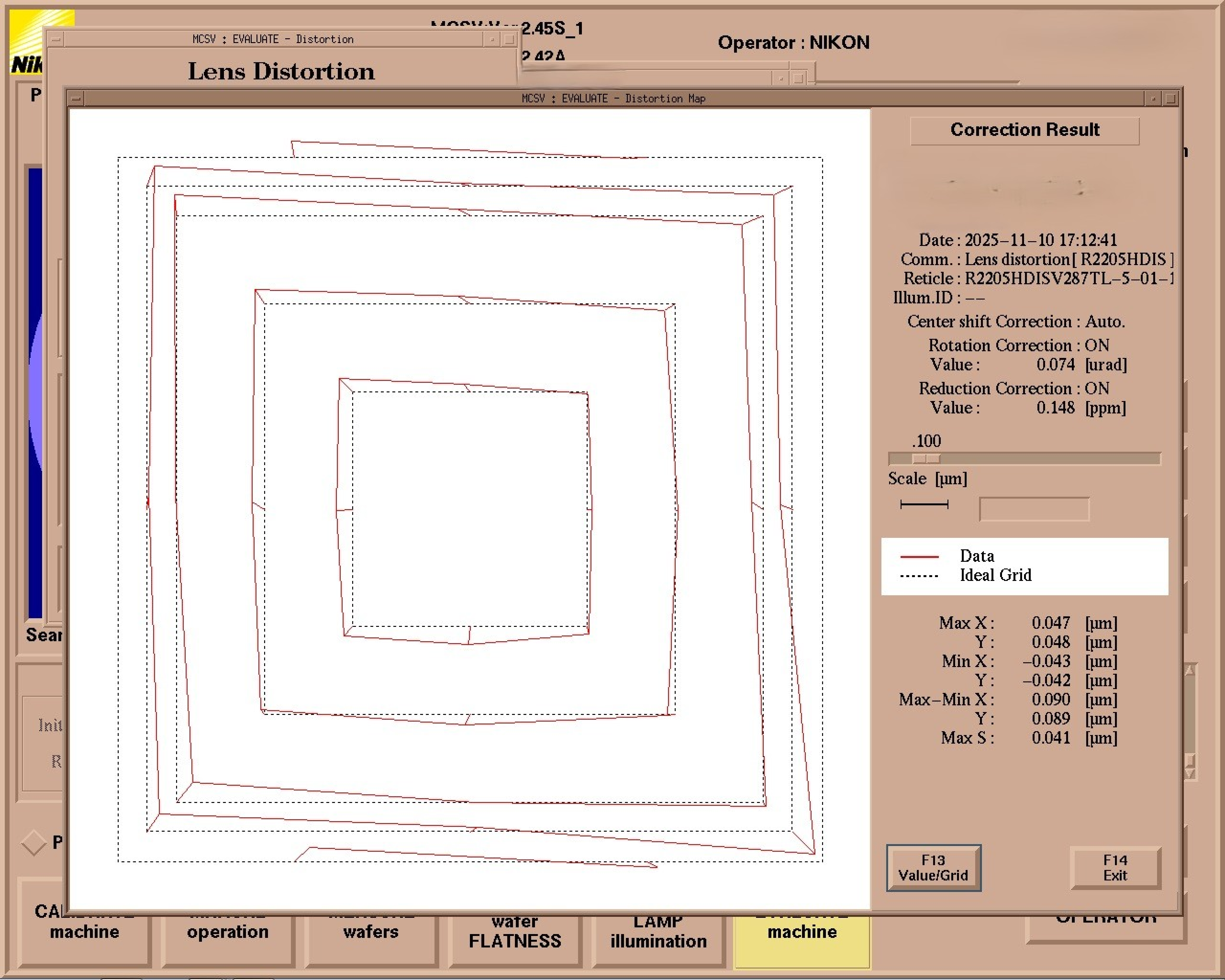
MOOV



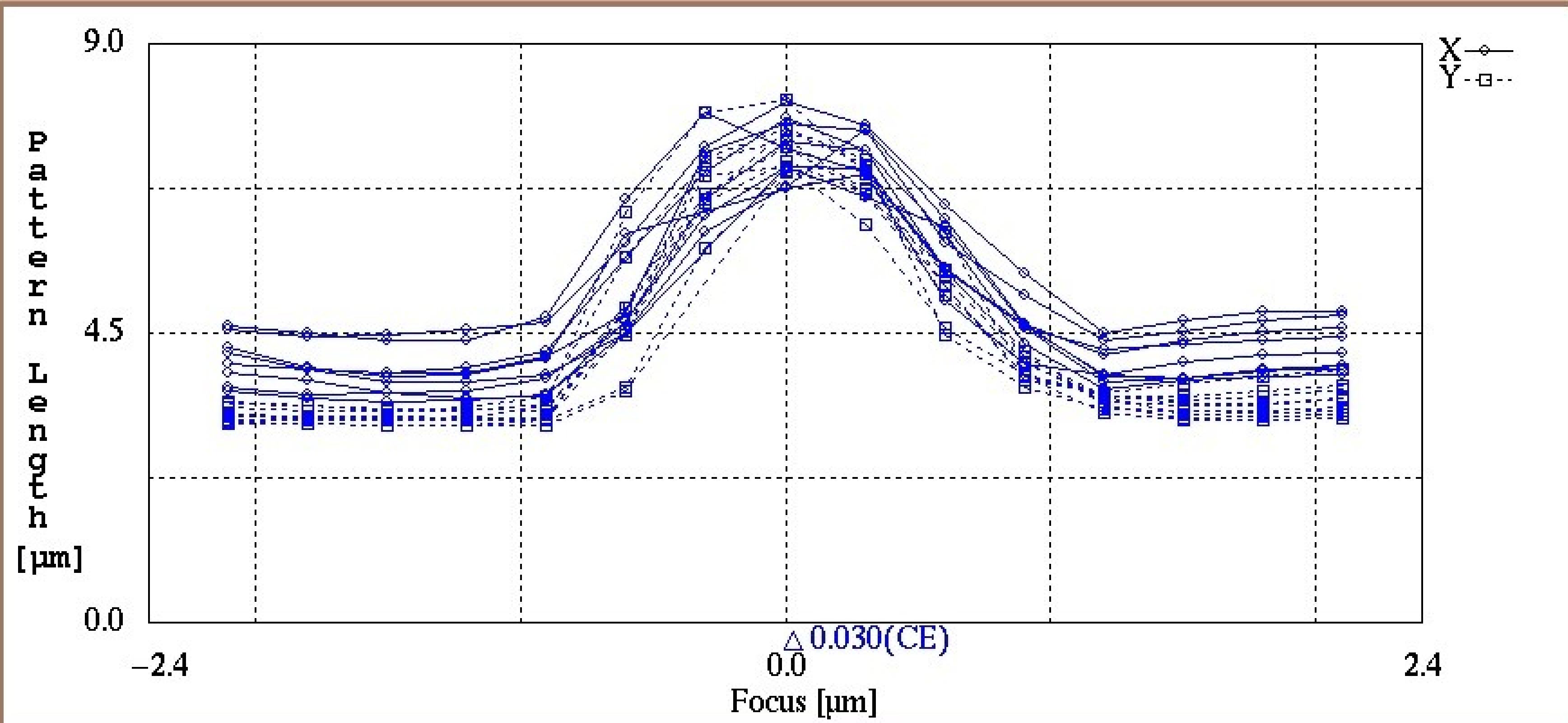
Operator : NIKON
MOSV : EVALUATE - Distortion
Lens Distortion
Correction Result
Meas.P.P.
Cond.file
Res.file
Mac.ID
Date
Comm. : Lens distortion[R2205HDIS]
Reticle : R2205HDISV287TL-5-01-1
Illum.ID : --
Center shift Correction : Auto.
Rotation Correction : ON
Value : 0.074 [urad]
Reduction Correction : ON
Value : 0.148 [ppm]
Address X : -6000 [µm]
Y : 12000 [µm]
Max X : 0.047 [µm]
Y : 0.048 [µm]
Min X : -0.043 [µm]
Y : -0.042 [µm]
Max-Min X : 0.090 [µm]
Y : 0.089 [µm]
Max S : 0.041 [µm]
F13 Value/Grid
F14 Exit
machine
operation
wafers
wafer FLATNESS
LAMP illumination
machine


MCSV : EVALUATE - Distortion
Lens Distortion
Operator : NIKON
MCSV : EVALUATE - Distortion Map
Correction Result
Date : 2025-11-10 17:12:41
Comm. : Lens distortion [R2205HDIS]
Reticle : R2205HDISV287TL-5-01-1
Illum.ID : --
Center shift Correction : Auto.
Rotation Correction : ON
Value : 0.074 [urad]
Reduction Correction : ON
Value : 0.148 [ppm]
.100
Scale [µm]
Data
Ideal Grid
Max X : 0.047 [µm]
Y : 0.048 [µm]
Min X : -0.043 [µm]
Y : -0.042 [µm]
Max-Min X : 0.090 [µm]
Y : 0.089 [µm]
Max S : 0.041 [µm]
F13 Value/Grid
F14 Exit
machine
operation
wafers
wafer FLATNESS
LAMP illumination
machine

MCSV : EVALUATE - Field Inclination

Field Inclination

No.	Locate [µm] X	Y	Best Focus [µm] V	H	V,H Ave.	V−H	Max Length [µm] X	Y	Inc. [µm]
1	−10701.00	−10701.00	0.085	0.091	0.088	−0.006	6.960	6.613	−0.021
2	−10700.00	0.00	0.006	−0.031	−0.013	0.037	6.603	6.443	−0.018
3	−10701.00	10701.00	0.012	0.102	0.057	−0.090	6.643	6.761	−0.016
4	0.00	−12000.00	−0.035	0.061	0.013	−0.096	7.603	7.494	−0.003
5	0.00	0.00	0.037	0.023	0.030	0.014	7.166	6.983	0.000
6	0.00	12000.00	0.010	0.101	0.055	−0.091	7.263	6.861	0.003
7	10701.00	−10701.00	0.141	0.149Mx	0.145	−0.008	6.780	6.437	0.016
8	10700.00	0.00	−0.012	−0.079Mn	−0.046	0.067	7.304	6.947	0.018
9	10701.00	10701.00	0.144	0.144	0.144	0.000	6.565	6.435	0.021



Comment : INC9 (0.35mic HV)[R2

Reject Limit (Upper) :	12.000 [µm]
Reject Limit (Range) :	1.000 [µm]
Approximate Reject Limit :	1.000 [µm]
Focus Center on Exposure :	0.000 [µm]
Focus Step on Exposure :	0.300 [µm]
Focus Slice Level :	1.000 [µm]
Weight Dumping Rate :	1.000
Angle adjustment Value X :	------- [µrad]
Y :	------- [µrad]
Angle X :	1.729 [µrad]
Angle Y :	0.225 [µrad]
Angle R :	−0.983 [µrad]
Angle P :	1.318 [µrad]
Max−Min :	0.228 [µm]
Curvature :	0.079 [µm]
UR−LL :	0.056 [µm]
UL−LR :	−0.088 [µm]

Object Wafer

Total

Each Wafer

1

Wafer No.

Prev

Next

F6 Param.

F7 List

F8 Summary

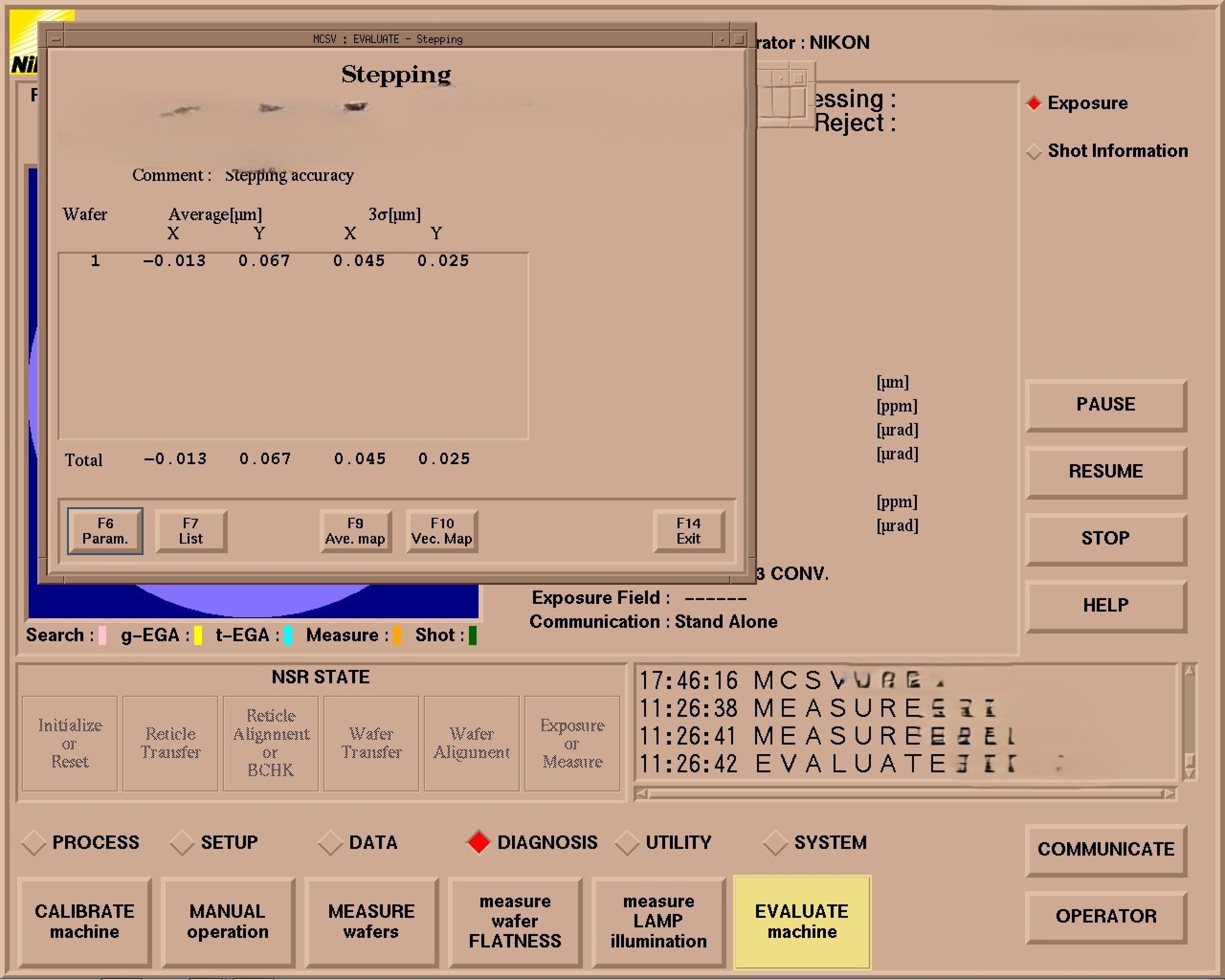
F9 Display

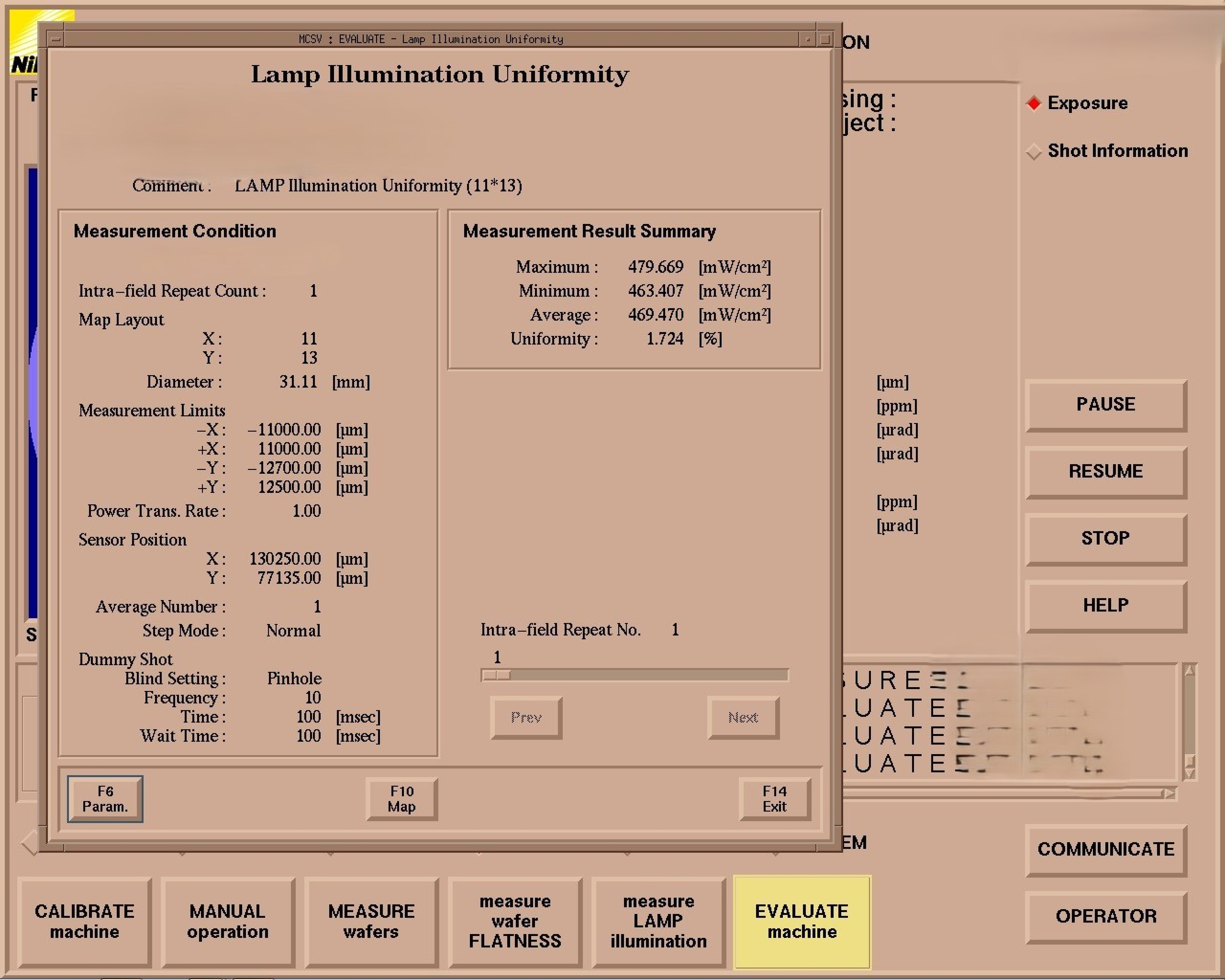
F10 Map

F14 Exit


MCSV : EVALUATE - LSA Base Line
LSA Base Line
Comment : Baseline check
Wafer
Average[μm]
X
Y
3σ[μm]
X
Y
1 0.032 -0.007 0.028 0.038
Total 0.032 -0.007 0.028 0.038
Total Average, 3σ
EGA Parameter
Shot Analysis
Map Display Mode
Measured Data
Correction Contents
Each Wafer
Offset X
Scaling X
Orthogonality
Shot Scaling
Offset Y
Scaling Y
Rotation
Shot Rotation
F6 Param
F7 List
F10 Map
F14 Exit
CALIBRATE machine
MANUAL operation
MEASURE wafers
measure wafer FLATNESS
measure LAMP illumination
EVALUATE machine
OPERATOR


MCSV : EVALUATE - LSA Base Line
LSA Base Line
Comment : Baseline check
Wafer
Average[µm]
X
Y
3σ[µm]
X
Y
1 −0.006 0.001 0.030 0.033
Total −0.006 0.001 0.030 0.033
Total Average, 3σ
EGA Parameter
Shot Analysis
Map Display Mode
Measured Data
Correction Contents
Each Wafer
Offset X
Scaling X
Orthogonality
Shot Scaling
Offset Y
Scaling Y
Rotation
Shot Rotation
F6 Param
F7 List
F10 Map
F14 Exit
CALIBRATE machine
MANUAL operation
MEASURE wafers
measure wafer FLATNESS
measure LAMP illumination
EVALUATE machine
OPERATOR


MCSV : EVALUATE - Stepping
Stepping
Comment : Stepping accuracy
Wafer
Average[μm]
3σ[μm]
X
Y
X
Y
1 -0.013 0.067 0.045 0.025
Total -0.013 0.067 0.045 0.025
F6 Param.
F7 List
F9 Ave. map
F10 Vec. Map
F14 Exit
rator : NIKON
essing :
Reject :
Exposure
Shot Information
[μm]
[ppm]
[μrad]
[μrad]
[ppm]
[μrad]
PAUSE
RESUME
STOP
HELP
3 CONV.
Exposure Field : ------
Communication : Stand Alone
Search :
g-EGA :
t-EGA :
Measure :
Shot :
NSR STATE
Initialize or Reset
Reticle Transfer
Reticle Alignment or BCHK
Wafer Transfer
Wafer Alignment
Exposure or Measure
17:46:16 MCSV
11:26:38 MEASURE
11:26:41 MEASURE
11:26:42 EVALUATE
PROCESS
SETUP
DATA
DIAGNOSIS
UTILITY
SYSTEM
COMMUNICATE
CALIBRATE machine
MANUAL operation
MEASURE wafers
measure wafer FLATNESS
measure LAMP illumination
EVALUATE machine
OPERATOR


MCSV : EVALUATE - Lamp Illumination Uniformity
Lamp Illumination Uniformity
Comment : LAMP Illumination Uniformity (11*13)
Measurement Condition
Intra-field Repeat Count : 1
Map Layout
X : 11
Y : 13
Diameter : 31.11 [mm]
Measurement Limits
-X : -11000.00 [µm]
+X : 11000.00 [µm]
-Y : -12700.00 [µm]
+Y : 12500.00 [µm]
Power Trans. Rate : 1.00
Sensor Position
X : 130250.00 [µm]
Y : 77135.00 [µm]
Average Number : 1
Step Mode : Normal
Dummy Shot
Blind Setting : Pinhole
Frequency : 10
Time : 100 [msec]
Wait Time : 100 [msec]
Measurement Result Summary
Maximum : 479.669 [mW/cm²]
Minimum : 463.407 [mW/cm²]
Average : 469.470 [mW/cm²]
Uniformity : 1.724 [%]
Intra-field Repeat No. 1
1
Prev
Next
F6 Param.
F10 Map
F14 Exit
Exposure
Shot Information
PAUSE
RESUME
STOP
HELP
COMMUNICATE
OPERATOR
CALIBRATE machine
MANUAL operation
MEASURE wafers
measure wafer FLATNESS
measure LAMP illumination
EVALUATE machine

MCSV : EVALUATE - Lamp Illumination Uniformity

MCSV : EVALUATE - Lamp Map

	1	2	3	4	5	6	7	8	9	10	11
1		474	472	471	471	471	472	474	476	479	
2	474	471	468	468	468	468	468	470	472	476	MAX 479
3	472	468	467	466	467	467	468	469	470	473	476
4	470	468	466	465	466	467	467	469	470	472	475
5	470	467	465	465	465	466	467	468	469	472	474
6	469	467	465	465	465	468	467	467	469	471	474
7	469	466	465	464	465	467	467	468	469	472	473
8	469	465	464	463	464	465	466	467	469	471	473
9	469	466	464	MIN 463	464	464	466	467	469	471	474
10	470	467	463	463	463	465	467	468	470	472	474
11	472	468	465	465	465	466	467	468	470	473	475
12	474	471	468	467	467	467	468	470	471	474	477
13		475	471	470	468	469	469	471	473	477	

Lamp Illumination Uniformity

Comm. : LAMP Illumination Unifo

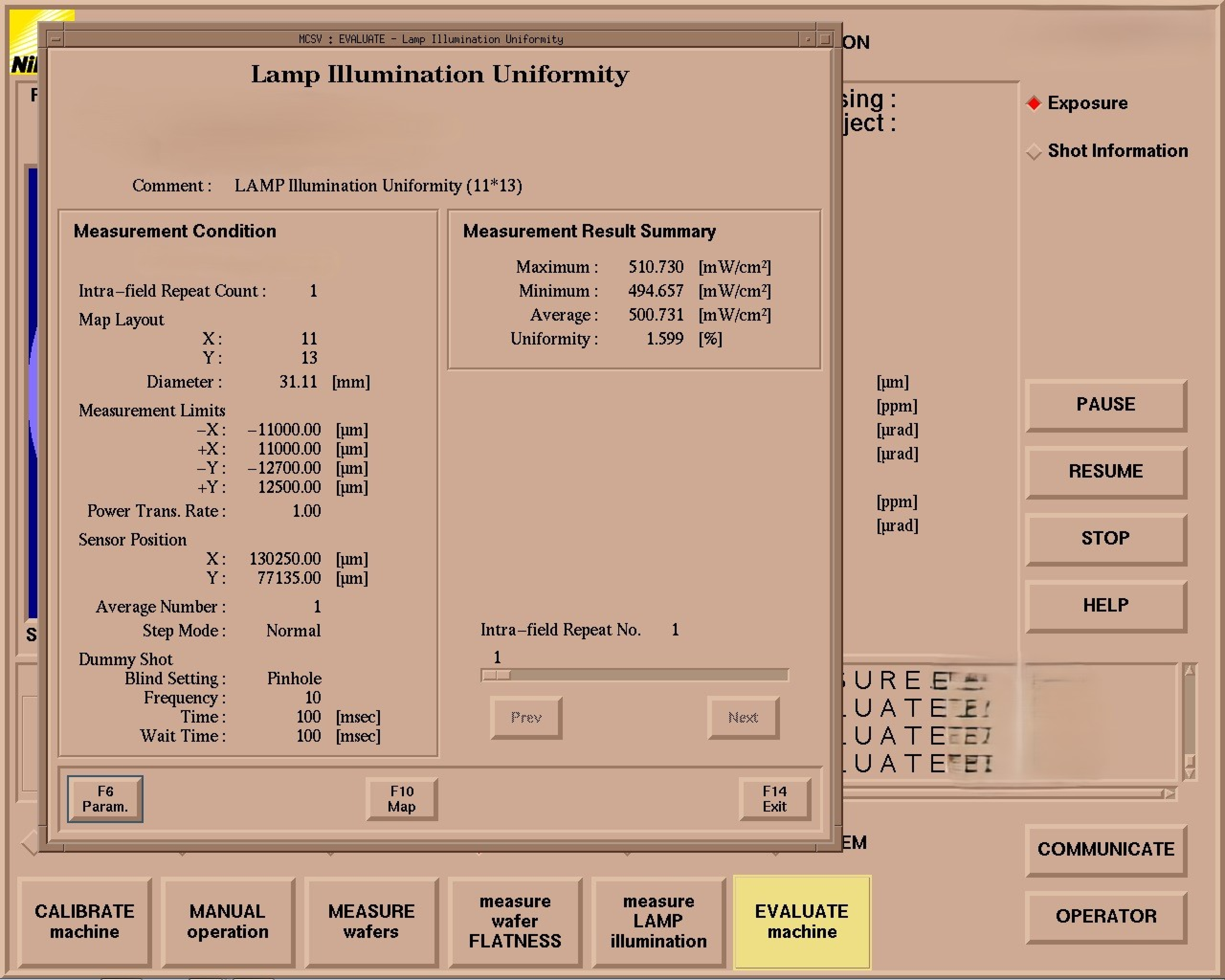
Maximum : 479.669 [mW/cm²]
Minimum : 463.407 [mW/cm²]
Average : 469.470 [mW/cm²]
Uniformity : 1.724 [%]

Intra–field Repeat Count : 1
Intra–field Repeat No. 1

477.5
475.5
473.5
471.5
469.5
467.5
465.5
463.5
461.5 [mW/cm²]

Disp. Mode
- Detail
- Summary
- 3D

F14
Exit


MCSV : EVALUATE - Lamp Illumination Uniformity
Lamp Illumination Uniformity
Comment : LAMP Illumination Uniformity (11*13)
Measurement Condition
Intra-field Repeat Count : 1
Map Layout
X : 11
Y : 13
Diameter : 31.11 [mm]
Measurement Limits
-X : -11000.00 [µm]
+X : 11000.00 [µm]
-Y : -12700.00 [µm]
+Y : 12500.00 [µm]
Power Trans. Rate : 1.00
Sensor Position
X : 130250.00 [µm]
Y : 77135.00 [µm]
Average Number : 1
Step Mode : Normal
Dummy Shot
Blind Setting : Pinhole
Frequency : 10
Time : 100 [msec]
Wait Time : 100 [msec]
Measurement Result Summary
Maximum : 510.730 [mW/cm²]
Minimum : 494.657 [mW/cm²]
Average : 500.731 [mW/cm²]
Uniformity : 1.599 [%]
Intra-field Repeat No. 1
1
Prev
Next
F6 Param.
F10 Map
F14 Exit
Exposure
Shot Information
PAUSE
RESUME
STOP
HELP
COMMUNICATE
OPERATOR
CALIBRATE machine
MANUAL operation
MEASURE wafers
measure wafer FLATNESS
measure LAMP illumination
EVALUATE machine